# **Plastic-Encapsulate Transistors**



## 2N3906 TRANSISTOR(PNP)

#### **FEATURE**

- PNP silicon epitaxial planar transistor for switching and Amplifier applications.
- As complementary type, the NPN transistor 2N3904 is recommended.
- This transistor is also available in the SOT-23 case with the type designation MMBT3906.



Package TO-92

## **MAXIMUM RATINGS**\* (T<sub>a</sub>=25°C unless otherwise noted)

Parameter	Symbol	Value	UNIT
Collector-Base Voltage	$V_{CBO}$	-40	V
Collector-Emitter Voltage	<b>V</b> CEO	-40	V
Emitter-Base Voltage	<b>V</b> <sub>EBO</sub>	-5	V
Collector Current -Continuous	<b>I</b> c	-0.2	Α
Collector Power Dissipation	Pc	0.625	W
Junction Temperature	<b>T</b> ₁	150	°C
Junction and Storage Temperature	<b>T</b> <sub>stg</sub>	-55~+150	°C

<sup>\*</sup>These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

### **ELECTRICAL CHARACTERISTICS** (T<sub>a</sub>=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =-10μA, I <sub>E</sub> =0	-40			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =-1mA, I <sub>B</sub> =0	-40			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =-10μA, I <sub>C</sub> =0	-5			<b>V</b>
Collector cut-off current	<b>I</b> CBO	V <sub>CB</sub> =-40V, I <sub>E</sub> =0			-0.1	μΑ
Collector cut-off current	I <sub>CEX</sub>	$V_{CE}$ =-30V, $V_{BE(OFF)}$ =-3V			-50	nA
Emitter cut-off current	<b>I</b> EBO	$V_{EB}$ =-5V, $I_{C}$ =0			-0.1	μΑ
	h <sub>FE(1)</sub>	V <sub>CE</sub> =-1V, I <sub>C</sub> =-10mA	100		400	
DC current gain	<b>h</b> <sub>FE(2)</sub>	V <sub>CE</sub> =-1V, I <sub>C</sub> =-50mA	60			
	<b>h</b> <sub>FE(3)</sub>	V <sub>CE</sub> =-1V, I <sub>C</sub> =-100mA	30			
Collector-emitter saturation voltage	<b>V</b> <sub>CE(sat)</sub>	$I_C$ =-50mA, $I_B$ =-5mA			-0.4	>
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	$I_C$ =-50mA, $I_B$ =-5mA			-0.95	<b>V</b>
Transition frequency	f⊤	V <sub>CE</sub> =-20V, I <sub>C</sub> =-10mA, f=100MHz	250			MHz
Delay time	<b>T</b> D	$V_{CC}$ =-3V, $V_{BE}$ =-0.5V,			35	ns
Rise time	$T_{R}$	I <sub>C</sub> =-10mA, I <sub>B1</sub> =-1mA			35	ns
Storage time	$T_{\text{stg}}$	V <sub>CC</sub> =-3V, I <sub>C</sub> =-10mA,			225	ns
Fall time	T <sub>F</sub>	I <sub>B1</sub> =I <sub>B2</sub> =-1mA			75	ns

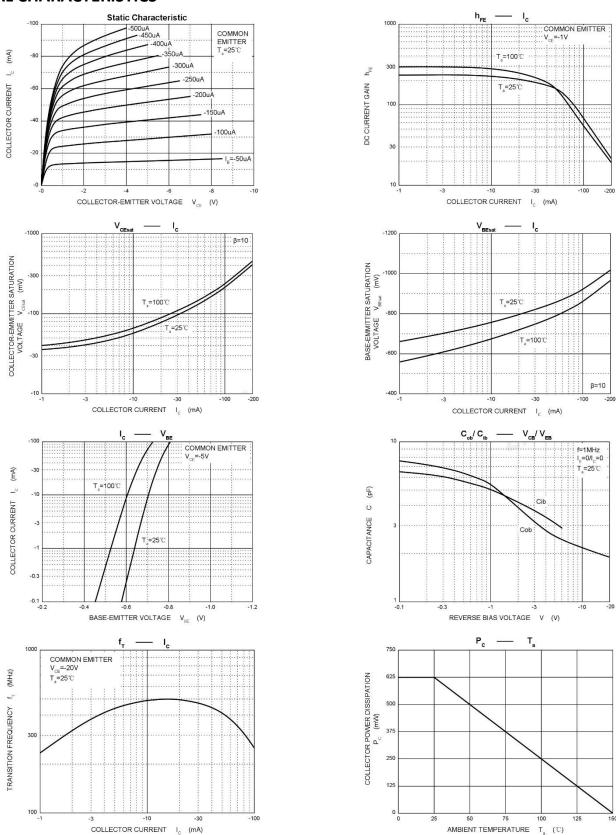
#### **CLASSIFICATION OF h**<sub>FE1</sub>

Rank	0	Y	G
Range	100-200	200-300	300-400

All products, product specifications and data are subject to change without notice to improve reliability, function or design or otherwise.

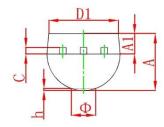


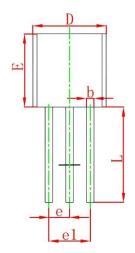
## **TYPICAL CHARACTERISTICS**





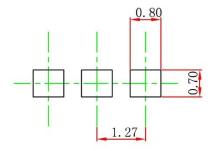
## **TO-92 Package Outline Dimensions**





Cumphal	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	3.300	3.700	0.130	0.146	
A1	1.100	1.400	0.043	0.055	
b	0.380	0.550	0.015	0.022	
С	0.360	0.510	0.014	0.020	
D	4.300	4.700	0.169	0.185	
D1	3.430		0.135		
E	4.300	4.700	0.169	0.185	
е	1.27	1.270 TYP		0.050 TYP	
e1	2.440	2.640	0.096	0.104	
L	14.100	14.500	0.555	0.571	
Φ		1.600		0.063	
h	0.000	0.380	0.000	0.015	

## **TO-92 Suggested Pad Layout**



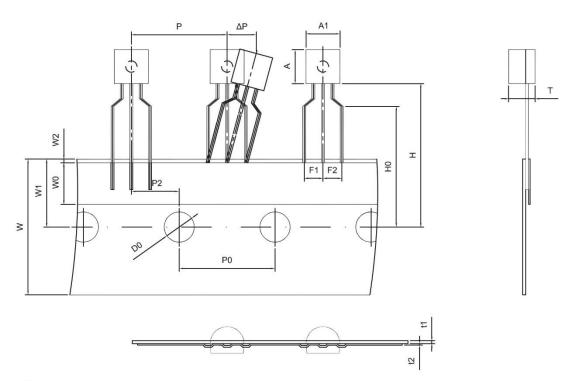
#### Note:

- 1. Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
- 3. The pad layout is for reference purposes only.

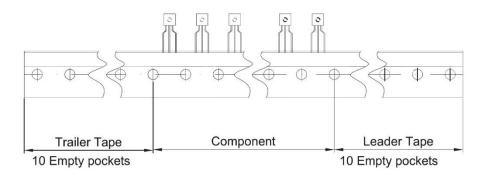


## **TO-92 Tape and Reel**

#### TO-92 PACKAGE TAPEING DIMENSION



	Dimiensions are in millimeter							
A1	A1 A T P P0 P2 F1 F2 W							
4.5	4.5	3.5	12.7	12.7	6.35	2.5	2.5	18.0
W0	W1	W2	Н	H0	D0	t1	t2	ΔΡ
6.0	9.0	1.0 MAX.	19.0	16.0	4.0	0.4	0.2	0



Package	Box	Box Size(mm)	Carton	Carton Size(mm)
TO-92	2000 pcs	333×162×43	20,000 pcs	350×340×250

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